

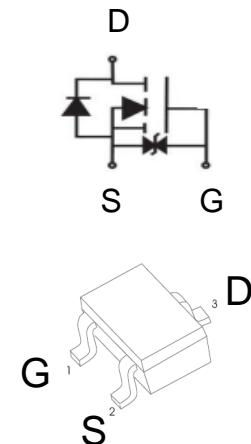


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MT2302ET N-Channel MOSFET

Feature

- 20V N-Channel MOSFET High Dense Design.
- $R_{DS(ON)} = 280\text{m}\Omega$ (typ.) @ $V_{GS} = 4.5\text{V}$
- $R_{DS(ON)} = 360\text{m}\Omega$ (typ.) @ $V_{GS} = 2.5\text{V}$
- Reliable and Rugged
- ESD Protected



Applications

- Portable Equipment and Battery Power Systems

MARKING: S2

SOT-523

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 8	
I_D	Continue Drain Current	0.82	A
I_{DM}	Pulsed Drain Current	1.9	
I_S	Diode Continuous Forward Current	0.27	A
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient(SOT23)	350	$^\circ\text{C/W}$

Static Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition				Unit
			Min.	Typ.	Max.	
Static Characteristics*						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_{DS}=250\mu\text{A}$	20	-	-	V
I_{DS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$T_J=85^\circ\text{C}$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	0.45	0.75	1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$	-	-	± 10	μA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=4.5\text{V}, I_{DS}=0.5\text{A}$	-	280	420	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_{DS}=0.3\text{A}$	-	360	585	
V_{SD}	Diode Forward Voltage	$I_{SD}=0.5\text{A}, V_{GS}=0\text{V}$	-	0.7	1.3	V

*Note:

a : Current maybe limit by junction temperature.

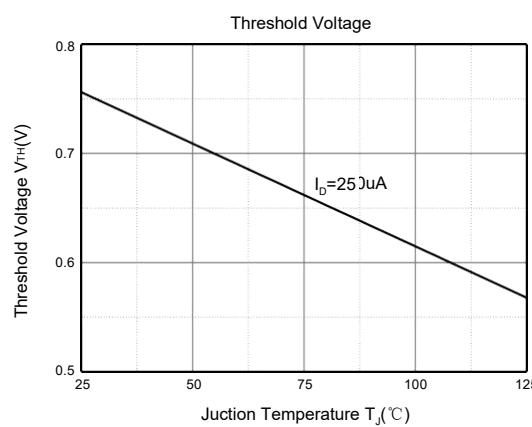
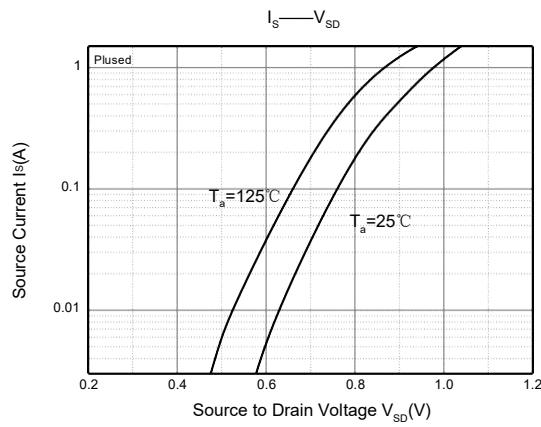
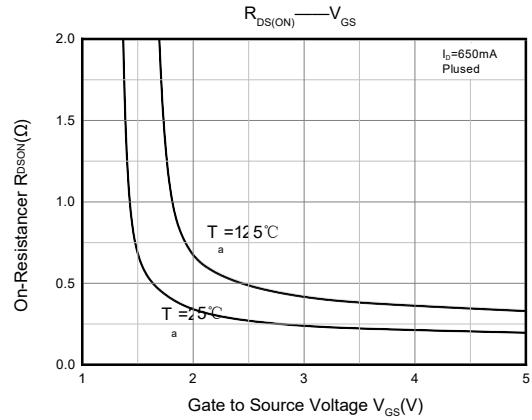
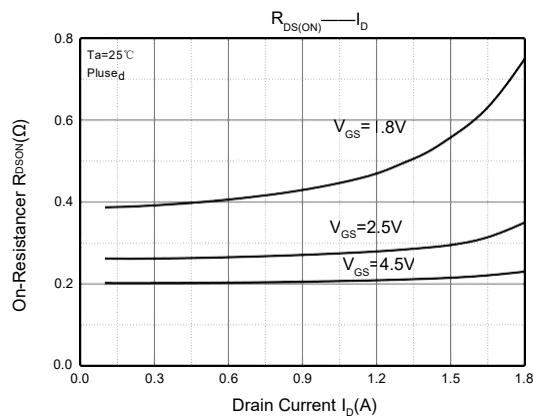
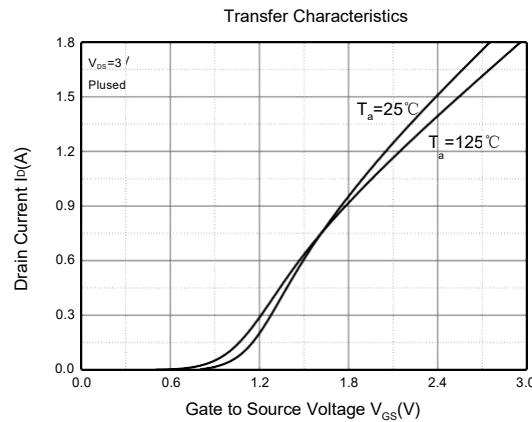
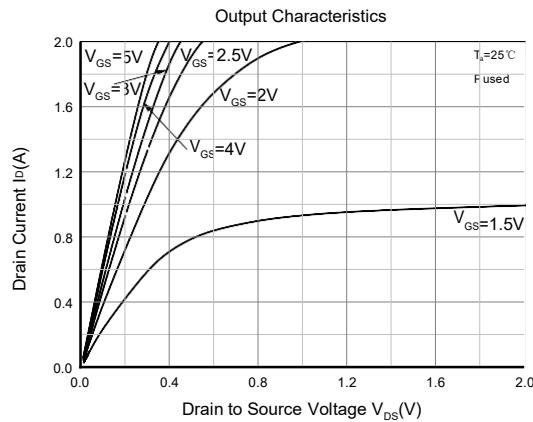
b : The $R_{\theta JC}$ is the sum of the thermal impedance from junction to ambient and depend on package type.

c : MOS static characteristics test by wafer level(CP).



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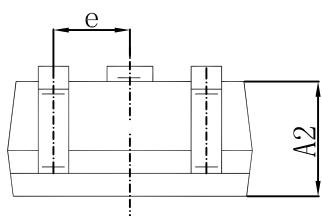
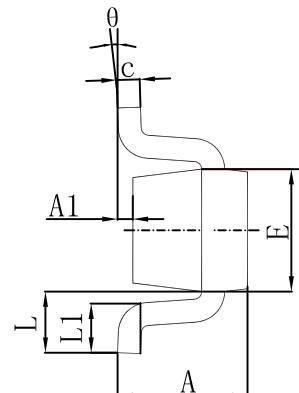
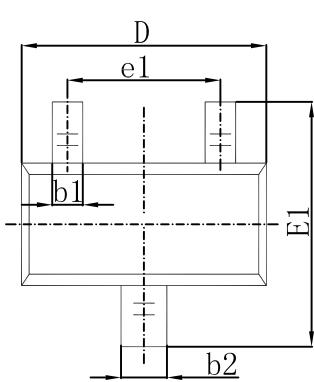
Typical Electrical and Thermal Characteristics





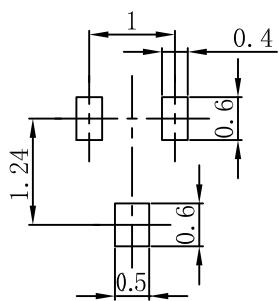
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SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.